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QUERY CONTROL FORM				RTIS USE ONLY	
Application No.	09/782,446	Prepared by	MPB	Tracking Number	0509 1147
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JACKET			
a. Serial No.	f. Foreign Priority	k. Print Claim(s)	p. PTO-1449
b. Applicant(s)	g. Disclaimer	l. Print Fig.	q. PTOL-85b
c. Continuing Data	h. Microfiche Appendix	m. Searched Column	r. Abstract
d. PCT	i. Title	n. PTO-270/328	s. Sheets/Figs
e. Domestic Priority	j. Claims Allowed	o. PTO-892	t. Other

SPECIFICATION

a. Page Missing
b. Text Continuity
c. Holes through Data
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f. Duplicate Text
g. Brief Description
h. Sequence Listing
i. Appendix
j. Amendments
k. Other

CLAIMS

a. Claim(s) Missing
b. Improper Dependency
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g. Amendments
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MESSAGE

Claim 3 (originally claim 25) depends on a cancelled claim 1 - original claim 1.

Please advise/correct claim dependency.

Thanh Vinh

initials

RESPONSE

initials

placing the substrate in an etching chamber;

providing an etchant gas comprising NH3 into the etching chamber with a flow rate from about 300 sccm to about 800 sccm;

generating a plasma from the NH3, which etches the organic dielectric layer; and

maintaining the substrate at a temperature between about 10° C to about 40° C during the etching of the organic dielectric layer.

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25. (Previously Presented) The method, as recited in claim 1, further comprising providing a bias power of between about 0 W and 100 W during etching of the organic dielectric layer.

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26. (Previously Presented) The method, as recited in claim 13, further comprising providing a bias power of between about 0 W and 100 W during etching of the organic low-k dielectric layer.

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27. (Previously Presented) The method, as recited in claim 13, further comprising:

placing an etch stop layer over the organic low-k dielectric layer;

placing a second organic low-k dielectric layer over the etch stop layer, wherein the second organic low-k dielectric layer is between the organic low-k dielectric layer and the hardmask.

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28. (Previously Presented) The method, as recited in claim 27, further comprising etching the second organic low-k dielectric layer with a first etch, wherein the first etch provides a bias power of between about 250 W to about 2500 W before selectively etching the organic low-k dielectric layer.